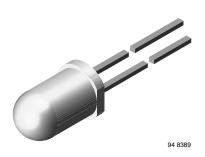
GREEN



## Vishay Semiconductors

# High Speed Infrared Emitting Diode, 850 nm, **GaAlAs Double Hetero**



### **DESCRIPTION**

TSHG6200 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### **FEATURES**

· Package type: leaded • Package form: T-1% • Dimensions (in mm): Ø 5

Peak wavelength: λ<sub>p</sub> = 850 nm

High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity:  $\varphi = \pm 10^{\circ}$ 

· Low forward voltage

· Suitable for high pulse current operation

• High modulation bandwidth: f<sub>c</sub> = 18 MHz

· Good spectral matching with CMOS cameras

· Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### Note

Please see document "Vishay Material Category Policy": www.vishav.com/doc?99902

#### **APPLICATIONS**

- Infrared radiation source for operation with CMOS cameras
- · High speed IR data transmission

| PRODUCT SUMMARY |                        |                                |     |         |  |
|-----------------|------------------------|--------------------------------|-----|---------|--|
| COMPONENT       | I <sub>e</sub> (mW/sr) | I <sub>e</sub> (mW/sr) φ (deg) |     | tr (ns) |  |
| TSHG6200        | 180                    | ± 10                           | 850 | 20      |  |

#### Note

· Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION |           |                              |              |  |  |
|----------------------|-----------|------------------------------|--------------|--|--|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |  |  |
| TSHG6200             | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1¾         |  |  |

#### Note

MOQ: minimum order quantity

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |   |                   |               |      |  |
|--|---|-------------------|---------------|------|--|
| PARAMETER  | TEST CONDITION                            | SYMBOL            | VALUE         | UNIT |  |
| Reverse voltage  |   | V <sub>R</sub>    | 5             | V    |  |
| Forward current  |   | I <sub>F</sub>    | 100           | mA   |  |
| Peak forward current   | $t_p/T = 0.5, t_p = 100 \mu s$            | I <sub>FM</sub>   | 200           | mA   |  |
| Surge forward current  | t <sub>p</sub> = 100 μs                   | I <sub>FSM</sub>  | 1             | Α    |  |
| Power dissipation  |   | P <sub>V</sub>    | 180           | mW   |  |
| Junction temperature   |   | T <sub>j</sub>    | 100           | °C   |  |
| Operating temperature range  |   | T <sub>amb</sub>  | - 40 to + 85  | °C   |  |
| Storage temperature range  |   | T <sub>stg</sub>  | - 40 to + 100 | °C   |  |
| Soldering temperature  | $t \le 5$ s, 2 mm from case               | T <sub>sd</sub>   | 260           | °C   |  |
| Thermal resistance junction/ambient  | J-STD-051, leads 7 mm,<br>soldered on PCB | R <sub>thJA</sub> | 230           | K/W  |  |





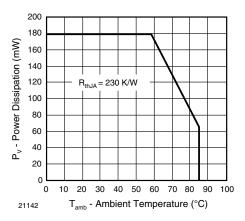


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

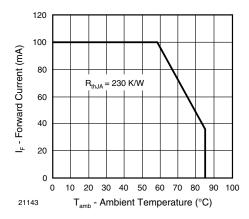


Fig. 1 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified) |   |                  |      |        |      |       |
|--|---|------------------|------|--------|------|-------|
| PARAMETER  | TEST CONDITION                                      | SYMBOL           | MIN. | TYP.   | MAX. | UNIT  |
| Forward voltage  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$         | V <sub>F</sub>   |      | 1.5    | 1.8  | V     |
|  | $I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$        | V <sub>F</sub>   |      | 2.3    |      | V     |
| Temperature coefficient of V <sub>F</sub>                                    | I <sub>F</sub> = 1 mA                               | TK <sub>VF</sub> |      | - 1.8  |      | mV/K  |
| Reverse current  | V <sub>R</sub> = 5 V                                | I <sub>R</sub>   |      |        | 10   | μΑ    |
| Junction capacitance   | $V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$     | Cj               |      | 125    |      | pF    |
| Dedicatists site.  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$         | I <sub>e</sub>   | 120  | 180    | 360  | mW/sr |
| Radiant intensity  | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs       | l <sub>e</sub>   |      | 1800   |      | mW/sr |
| Radiant power  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$         | φ <sub>e</sub>   |      | 50     |      | mW    |
| Temperature coefficient of φ <sub>e</sub>                                    | I <sub>F</sub> = 100 mA                             | TKφ <sub>e</sub> |      | - 0.35 |      | %/K   |
| Angle of half intensity  |   | φ                |      | ± 10   |      | deg   |
| Peak wavelength  | I <sub>F</sub> = 100 mA                             | $\lambda_{p}$    |      | 850    |      | nm    |
| Spectral bandwidth   | I <sub>F</sub> = 100 mA                             | Δλ               |      | 40     |      | nm    |
| Temperature coefficient of $\lambda_p$                                       | I <sub>F</sub> = 100 mA                             | TKλ <sub>p</sub> |      | 0.25   |      | nm/K  |
| Rise time  | I <sub>F</sub> = 100 mA                             | t <sub>r</sub>   |      | 20     |      | ns    |
| Fall time  | I <sub>F</sub> = 100 mA                             | t <sub>f</sub>   |      | 13     |      | ns    |
| Cut-off frequency  | I <sub>DC</sub> = 70 mA, I <sub>AC</sub> = 30 mA pp | f <sub>c</sub>   |      | 18     |      | MHz   |
| Virtual source diameter  |   | d                |      | 3.7    |      | mm    |

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### **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

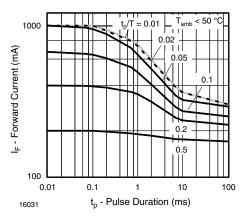


Fig. 2 - Pulse Forward Current vs. Pulse Duration

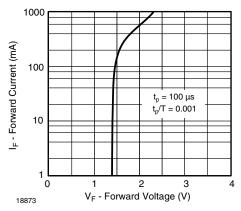


Fig. 3 - Forward Current vs. Forward Voltage

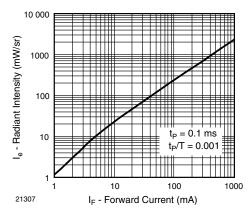


Fig. 4 - Radiant Intensity vs. Forward Current

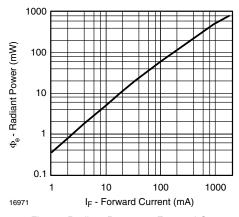


Fig. 5 - Radiant Power vs. Forward Current

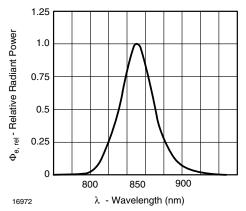


Fig. 6 - Relative Radiant Power vs. Wavelength

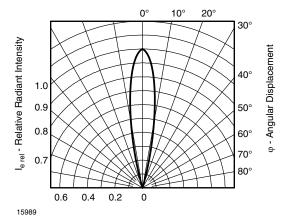
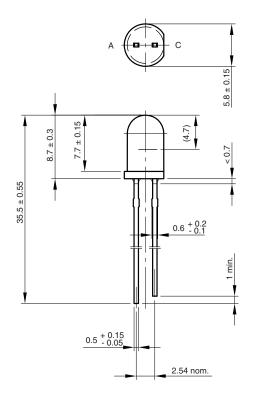


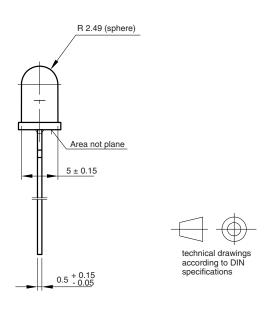
Fig. 7 - Relative Radiant Intensity vs. Angular Displacement





### **PACKAGE DIMENSIONS** in millimeters





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